L Number	Hits		DB	Time stamp
-	92	("257/168").CCLS.	USPAT;	2002/02/05 17:40
İ			US-PGPUB;	2002,02,03 1,.40
ļ			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	312	("257/173").CCLS.	USPAT;	2002/02/05 20:15
			US-PGPUB;	, , , , , , , , , , , , , , , , , , , ,
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	9	1 (USPAT;	2002/02/05 20:15
		('("257/173").CCLS.)	US-PGPUB;	
İ			EPO; JPO;	
			DERWENT;	
\ _	,	plumplifu odić bizalan sad nase to	IBM TDB	
ĺ	4	plurality adj2 bipolar adj transistor.clm. and esd	USPAT;	2002/02/05 20:16
		and esd	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	36	((("257/168").CCLS.) or	IBM TDB	
	30	(("257/173").CCLS.)) and esd and bipolar	USPAT;	2002/02/05 20:17
		adj transistor	US-PGPUB;	
		adj transistor	EPO; JPO;	
			DERWENT;	
_	40	(plurality adj2 bipolar adj	IBM TDB	0000 (00 (05 00 00
	10	transistor.clm. and esd) or	USPAT;	2002/02/05 20:22
		(((("257/168").CCLS.) or	US-PGPUB;	
		(("257/173").CCLS.)) and esd and bipolar	EPO; JPO;	
1		adj transistor)	DERWENT;	
_	547		IBM TDB USPAT:	2002/02/05 20 02
		transistor	US-PGPUB;	2002/02/05 20:23
			EPO; JPO;	
			DERWENT;	
	i		IBM TDB	
_	117	resistor and esd and ((parallel or	USPAT;	2002/02/05 20:34
		lateral\$2) near3 bipolar adj transistor)	US-PGPUB;	2002/02/03 20.34
		,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	152		EPO	2002/02/05 20:35
-	395	(("257/168").CCLS.) or (("257/173").CCLS.)	USPAT;	2002/02/06 10:57
,			US-PGPUB;	
			EPO; JPO;	1
			DERWENT;	
			IBM TDB	
-	166	(("257/168").CCLS.) or (("257/173").CCLS.)	USPAT;	2002/02/06 08:43
		and ((esd or electrostatic adj discharge)	US-PGPUB;	
į l		near12 protect\$3)	EPO; JPO;	
			DERWENT;	
		/ / // 057 / 1 60 // 2 22 2	IBM TDB	
-	97	(("257/168").CCLS.) or (("257/173").CCLS.)	USPAT;	2002/02/06 08:47
	ĺ	and ((esd or electrostatic adj discharge)	US-PGPUB;	
		near12 protect\$3) and (resist\$3 near15	EPO; JPO;	
		bipolar adj transistor)	DERWENT;	
_		// 257 /1 (0)	IBM TDB	
	94	(("257/168").CCLS.) or (("257/173").CCLS.)	USPAT;	2002/02/06 08:48
		and ((esd or electrostatic adj discharge)	US-PGPUB;	
ĺ		near12 protect\$3) and (resist\$3 near15	EPO; JPO;	
		bipolar adj transistor) and (plurality near12 transistor)	DERWENT;	
_	94	(("257/168").CCLS.) or (("257/173").CCLS.)	IBM TDB	0000 (00 (6 = ==========================
Ī	94	and ((esd or electrostatic adj discharge)	USPAT;	2002/02/06 08:51
	ļ	near12 protect\$3) and (resist\$3 near15	US-PGPUB;	
-		bipolar adj transistor) and (plurality	EPO; JPO;	
	1	near12 transistor) and (parallel near12	DERWENT;	
	İ	(transistor or connect\$3 or load))	IBM TDB	
L		, TTTTTTTTTTTTTTTTTTTTTTTTTTTTTTTTTTTT		

393 (("257/168").CCLS.) or ("257/173").CCLS.) and (lead or elactrostatic add discharge) lear12 protects3) and (resist53 mear15 bipolar add) transistor and (plurality chromostor) and (plurality chromostor) and (lead or elactrostatic add discharge) near12 protects3) and (resist53 mear15 bipolar add) transistor) and (plurality near12 transistor) and (plurality near12 transistor) and (plurality near12 transistor) and (plurality near12 transistor) and (plurality near12 transistor) and (plurality near12 protects3) and (resist53 mear15 bipolar.tir, ab. and (ic or integrated add) and circuit) and (lead or elactrostatic add) discharge) near12 protects3) and (resist3 mear15 bipolar.tir, ab. and (ic or integrated add) circuit) and (lead or electrostatic add) discharge) near12 protects3) and (resist53 mear15 bipolar.tir, ab. and (ic or integrated add) circuit) and bus (("257/168").CCLS.) or ("257/173").CCLS.) and (lead or electrostatic add) discharge) near12 protects3) and (resist53 near15 bipolar add) transistor) and (plurality near12 transistor) near12 transistor) near12 transistor) near12 transistor) near12 transistor					
	_	93	and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality	US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 08:51
- 93 (("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) USPAT;			(transistor or connect\$3 or load))and	IBM TDB	
circuit and ((esd or electrostatic adj discharge)	-	93	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect\$3 or load))and	US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 08:52
- 93 (ircuit) and bus and (r257/173").CCLS.) and (esd or electrostatic adj discharge) near12 protect3) and (resists) near15 bipolar adj transistor) and (plurality near12 protect3) and (parallel near12 (transistor) connect3 or load)) and bipolar ti, ab. and (ic or integrated adj circuit) and bus (ircuit) and esd adj protect3.ti, ab.) and esd adj protect3.ti, ab. (ircuit) and esd adj protect3.ti, ab.) and bipolar adj2 transistor - 20 (((("257/168").CCLS.)) or (("257/173").CCLS.)) and esd adj protect3.ti, ab.) and bipolar adj2 transistor (ircuit) in the bus	-	93	circuit) (("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect\$3 or load))and	US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 08:54
- 31 circuit) and bus ((("257/168").CCLS.) or (("257/173").CCLS.)) and esd adj US-PGPUB; EPO, JPO; DERWENT; IBM TDB USPAT; (("257/168").CCLS.)) and esd adj US-PGPUB; Protect\$3.ti,ab. OR USPAT; US-PGPUB; Protect\$3.ti,ab.) and bipolar adj2 US-PGPUB; Protect\$3.ti,ab.) and bipolar adj2 US-PGPUB; Protect\$3.ti,ab.) and bipolar adj2 US-PGPUB; Protect\$3.ti,ab.) and bipolar adj2 US-PGPUB; Protect\$3.ti,ab.) and bipolar adj2 US-PGPUB; Protect\$3.ti,ab.) and bipolar adj2 US-PGPUB; Protect\$3.ti,ab.) and bipolar adj2 US-PGPUB; Protect\$3.ti,ab.) and bipolar adj2 US-PGPUB; Protect\$3.ti,ab.) and bipolar adj2 US-PGPUB; Protect\$3.ti,ab.) and bipolar adj2 US-PGPUB; Protect\$4.ti,ab.) and bipolar adj2 US-PGPUB; Protect\$5.ti,ab.) and bipolar adj2 US-PGPUB; Protect\$6.ti,ab. and US-PGPUB; P	-	93	circuit) and bus (("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect\$3 or load)) and	US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 08:54
- 20 (((('257/168").CCLS.)) or (("257/173").CCLS.)) and esd adj protect53.ti,ab.) and bipolar adj2 transistor ((('(257/168").CCLS.)) or (("257/173").CCLS.)) or (("257/173").CCLS.)) or (("257/173").CCLS.)) and esd adj USPAT; (("257/173").CCLS.)) and esd adj USPAT; (US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	_	31	circuit) and bus ((("257/168").CCLS.) or (("257/173").CCLS.)) and esd adj	US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 08:57
- 16 ((((("257/168").CCLS.) or ("257/173").CCLS.)) and esd adj protect\$3.ti,ab.) and bipolar adj2 transistor) and resist\$3 - 3 5043782.pn. 5043782.pn. 2 5708550.pn. 2 5708550.pn. 2 jp-61292351\$-\$.did. - 2 jp-61292351\$-\$.did. - 395 (("257/168") or ("257/173")).CCLS. - 0 ("L3 and esd adj2 protection.ti,ab.").PN. - 0 ("L3 and esd adj2 protection.ti,ab.").PN. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT	-	20	(("257/173").CCLS.)) and esd adj protect\$3.ti,ab.) and bipolar adj2	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 08:57
- 3 5043782.pn. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	-	16	(("257/173").CCLS.)) and esd adj protect\$3.ti,ab.) and bipolar adj2	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 09:14
- 2 5708550.pn. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	_	3	5043782.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 09:16
- 2 jp-61292351\$-\$.did. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	_	2	5708550.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 09:15
- 395 (("257/168") or ("257/173")).CCLS. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	_	2	jp-61292351\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 09:16
- 0 ("L3 and esd adj2 protection.ti,ab.").PN. USPAT; US-PGPUB; EPO; JPO; DERWENT;	_	395	(("257/168") or ("257/173")).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 11:37
	-	0	("L3 and esd adj2 protection.ti,ab.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 10:58

	29	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab.	USPAT; US-PGPUB; EPO; JPO;	2002/02/06 10:58
			DERWENT;	
-	7	esd adj2 protection.ti,ab. and	IBM TDB USPAT; US-PGPUB;	2002/02/06 10:59
	0	bipolar.ti,ab. ((("257/168") or ("257/173")).CCLS.) and	EPO; JPO; DERWENT; IBM TDB	0000 (00 (00 00
		esd adj2 protection.ti,ab. and bipolar.ti,ab. and plurality adj2 bipolar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 10:59
-	0	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar.ti,ab. and plurality adj2 transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 11:00
-	15	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar adj transistor	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 11:00
-	12	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar adj transistor and resist\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 11:02
-	5	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar adj transistor and resist\$3 and parallel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 11:02
_	3	((("257/168") or ("257/173")).CCLS.) and esd adj protection.ti,ab. and bipolar adj transistor.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 11:48
	131	esd adj protection.ti,ab. and bipolar adj transistor.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 11:49
_	1	esd adj protection.ti,ab. and bipolar adj transistor.ti,ab. and plurality adj2 (bipolar or transistor) and resist\$3 and parallel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 14:06
-	12	esd adj protection.ti,ab. and ((advantage or purpose) near10 \$3bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 14:08
~	1	("0708550").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 15:07
_	2	("5708550").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 15:35
_	7	(("5043782") or ("5708550") or ("6268639") or ("5329143") or ("6172404") or ("5623387") or ("5272371")).PN.	USPAT	2002/02/06 15:20

-	5	((("5043782") or ("5708550") or ("6268639") or ("5329143") or ("6172404") or ("5623387") or ("5272371")).PN.) and	USPAT; US-PGPUB; EPO; JPO;	2002/02/06 15:21
		(base adj region and bipolar adj transistor)	DERWENT; IBM TDB	
-	0	("esd adj protection.ti,ab and bipolar adj transistor.ti,ab. and path").PN.	USPAT; US-PGPUB; EPO; JPO;	2002/02/06 15:35
_	0	(TTT GG PTTTTTTTTTTTTTTTTTTTTTTTTTTTTT	DERWENT; IBM TDB USPAT;	2002/02/06 15:36
		adj transistor.ti,ab. and path").PN.	US-PGPUB; EPO; JPO; DERWENT;	
_	48	esd adj protection.ti,ab. and bipolar adj transistor.ti,ab. and path	IBM TDB USPAT; US-PGPUB; EPO; JPO;	2002/02/06 15:38
-	17	esd adj protection.ti,ab. and bipolar adj	DERWENT; IBM TDB USPAT;	2002/02/06 15:40
		transistor.ti,ab. and current adj path	US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 13:40
_	15	bipolar adj transistor and esd adj protection and (increase near12 path)	IBM TDB USPAT; US-PGPUB;	2002/02/06 16:49
			EPO; JPO; DERWENT; IBM TDB	
-	12	bipolar adj transistor and esd adj protection and ((base near10 (surround\$3 or enclos\$3)) near10 (emitter or collector))	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 17:01
-	710	bipolar adj transistor.ti,ab. and ((base near10 (surround\$3 or enclos\$3)) near10 (emitter or collector))	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 17:04
_	506	<pre>bipolar adj transistor.ti,ab. and ((base near5 (surround\$3 or enclos\$3)) near5 (emitter or collector))</pre>	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 17:05
_	334	<pre>bipolar adj transistor.ti,ab. and ((base near3 (surround\$3 or enclos\$3)) near3 (emitter or collector))</pre>	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 17:05
	2	bipolar adj transistor.ti,ab. and ((base near3 (surround\$3 or enclos\$3)) near3 (emitter or collector)) and esd.ti,ab. and protection.ti,ab.	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 17:07
_	5	bipolar adj transistor.ti,ab. and ((base near4 (surround\$3 or enclos\$3)) near4 (emitter or collector)) and (electrostatic adj discharge or esd).ti,ab. and	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 17:10
_	430	protection.ti,ab. bipolar adj transistor.ti,ab. and ((base near4 (surround\$3 or enclos\$3)) near4 (emitter or collector))	IBM TDB USPAT; US-PGPUB; EPO; JPO;	2002/02/06 17:11
-	6	bipolar adj transistor.ti,ab. and ((base near4 (surround\$3 or enclos\$3)) near4 (emitter or collector)) and (esd with	DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO;	2002/02/06 17:32
		protection)	DERWENT; IBM TDB	

	7		1-12-4	
_	997	("257/355").CCLS.	USPAT; US-PGPUB;	2002/02/06 17:33
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	95	i the second sec	USPAT;	2002/02/06 17:42
		and bipolar adj transistor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	4	((("257/355").CCLS.) and esd adj	IBM TDB	2002/02/06 17:39
ļ	1	protection and bipolar adj transistor) and	US-PGPUB;	2002/02/06 17:39
		((base near7 (surround\$3 or enclos\$3))	EPO; JPO;	
		near7 (emitter or collector))	DERWENT;	
			IBM TDB	
_	1115	(("257/360") or ("257/361") or ("257/362")	USPAT;	2002/02/06 17:38
		or ("257/363")).CCLS.	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
-	122	((("257/360") or ("257/361") or	USPAT;	2002/02/06 17:39
		("257/362") or ("257/363")).CCLS.) and esd	US-PGPUB;	2002/02/00 17:35
	1	adj protection and bipolar adj transistor	EPO; JPO;	
1	1		DERWENT;	
	Ì		IBM TDB	
_	6	, ,,,, ==-,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	USPAT;	2002/02/06 17:42
1		("257/362") or ("257/363")).CCLS.) and esd	US-PGPUB;	
		adj protection and bipolar adj transistor)	EPO; JPO;	
		<pre>and ((base near7 (surround\$3 or enclos\$3)) near7 (emitter or collector))</pre>	DERWENT;	
_	893	(("257/370") or ("257/373")).CCLS.	IBM TDB USPAT;	2002/02/06 17:41
		((237/370 / OI (237/373 //:ccd3.	US-PGPUB;	2002/02/08 17:41
			EPO; JPO;	İ
			DERWENT;	!
	_		IBM TDB	
-	7	((("257/370") or ("257/373")).CCLS.) and	USPAT;	2002/02/06 17:42
		esd adj protection and bipolar adj	US-PGPUB;	
		transistor	EPO; JPO;	
			DERWENT; IBM TDB	
-	0	(((("257/370") or ("257/373")).CCLS.) and	USPAT;	2002/02/06 18:25
		esd adj protection and bipolar adj	US-PGPUB;	
!		transistor) and ((base near7 (surround\$3	EPO; JPO;	
		or enclos\$3)) near7 (emitter or	DERWENT;	
]	100	collector))	IBM TDB	
-	192		USPAT;	2002/02/06 18:28
		adj2 well	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	65	bipolar adj transistor.ti. and second adj2	USPAT;	2002/02/06 18:42
		well	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		1-k-m-1 - at him-1-m - it is a first of the second	IBM TDB	0000 (00 (5 5) 5
-	2	lateral adj bipolar adj transistor.ti. and second adj2 well	USPAT;	2002/02/06 18:45
		second adjz well	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
- 1	15	lateral adj bipolar adj transistor.ti,ab.	USPAT;	2002/02/06 18:45
		and second adj2 well	US-PGPUB;	
		-	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	(source or drain) adj regions same	USPAT;	2002/02/07 08:33
		through-contact\$3	US-PGPUB;	
			EPO; JPO; DERWENT;	
ļ			IBM TDB	•
		· · · · · · · · · · · · · · · · · · ·	בחנו נותד	

-	3	formed adj2 "same substrate" same	USPAT;	2002/02/07 10:0	П
		plurality adj2 bipolar adj transistor	US-PGPUB;		
			EPO; JPO;]
			DERWENT;	†	- 1
			IBM TDB		
_	4	(("5623387") or ("5043782") or ("6075271") or ("6277689")).PN.	USPAT	2002/02/07 10:02	2
-	0	jp-0361292351\$-\$.did.	USPAT;	2002/02/07 10:04	1
			US-PGPUB;		
	1		EPO; JPO;	1	ſ
			DERWENT;	Í	
			IBM TDB	İ	
-	0	jp-361292351\$-\$.did.	USPAT;	2002/02/07 10:04	1
			US-PGPUB;		
			EPO; JPO;		- 1
	1		DERWENT;		
ĺ			IBM TDB		
-	2	jp-61292351\$-\$.did.	USPAT;	2002/02/07 10:04	1
			US-PGPUB;		
			EPO; JPO;		-
			DERWENT;	į	İ
			IBM TDB		